# Implementation of Grover's Algorithm based on Quantum Reservoir Computing

Shivani Mehta Department of ECE, IIITDM Kancheepuram, Chennai-600127, India. ec22m2002@iiitdm.ac.in Sajja Jyothikrishna Department of ECE, IIITDM Kancheepuram, Chennai-600127, India. ec21b1022@iiitdm.ac.in V.Praveen Bhallamudi

Department of Physics,

IIITDM Kancheepuram,

Chennai-600036, India.

praveen.bhallamudi@iitm.ac.in

Sumanth Arige Department of ECE, IIITDM Kancheepuram, Chennai-600127, India. edm20d010@iiitdm.ac.in

Tejendra Dixit, Member, IEEE

Department of ECE,

IIITDM Kancheepuram,

Chennai-600127, India.

tdixit@iiitdm.ac.in

Abstract—Quantum computing represents the leading edge of computational technology, leveraging the principles of quantum mechanics to execute targeted computations much faster than classical computers. In contrast to classical bits, which are limited to representing either 0 or 1, qubits, or quantum bits, exhibit the extraordinary property of superposition. This distinctive characteristic enables qubits to simultaneously occupy multiple states, empowering quantum computers to explore numerous potential solutions to a problem concurrently. This feature makes quantum computing particularly potent for specific tasks. Recent research endeavors have been sparked by the potential of advanced quantum computing technology, leading to the creation of simulations of quantum computers using classical hardware. Grover's quantum search algorithm serves as a notable illustration of quantum computing application, enabling quantum computers to conduct a database search within an unsorted array with a quadratic speedup in time efficiency compared to classical computers. This document presents the quantum Grover search algorithm and its application through 5-qubit quantum circuits, as well as a design framework to simplify the creation of an oracle for a greater number of qubits.

Keywords—Quantum computation, Qubits, Oracle, Grover's algorithm, IBM Qiskit.

## I. INTRODUCTION

The exploration of quantum computing [1][2] falls within the realm of quantum information science, which revolves around the fundamental principles of storing and manipulating information. In this work, we delved into quantum computing, acquiring a comprehensive understanding of quantum bits and their properties, as well as leveraging these properties to tackle problems. We familiarized ourselves with quantum gates and their operations on qubits, simulating all the fundamental quantum gates [3][4]. Additionally, we delved into the Grover search algorithm and implemented quantum gates for Grover operations. Quantum computers exhibit significantly faster speeds compared to classical computers [5][6]. In the case of an unsorted dataset with size N, classical computers usually demand O(N) operations, whereas Grover's algorithm accomplishes this task optimally in  $O(\sqrt{N})$  operations.

We executed the algorithm using Qiskit, an IBM tool for computing quantum circuits, and conducted simulations for the Grover algorithm [7], presenting the results graphically with the probability of obtaining the correct output.

Within Grover's quantum search algorithm, a network with n qubits harbors  $2^n = N$  states, with each state bearing a probability of 1/N for discovery. Consequently, the amplitude of each state is  $1/\sqrt{N}$ . Conversely, classical systems tackling the same problem necessitate a maximum of O(N) trials.

### II. BACKGROUND AND METHODOLOGY

The Grover search algorithm, conceived by Lov Grover in 1996, stands as a quantum computing method offering a quadratic acceleration compared to classical counterparts, particularly for solving unstructured search problems [8]. It has gained renown for its proficiency in searching through unsorted databases, but its utility extends to a spectrum of tasks, encompassing cryptographic problem-solving and quantum system simulation. This can speed up a search problem quadratically. For N number of unsorted data classical computer require O (N) operations Whereas Grover is optimal and can do this in  $O(\sqrt{N})$  operation. The following provides a synopsis of the workings of the Grover search algorithm [9]:

#### A. Initialisation

Commencing the process involves establishing a superposition of all conceivable states. For instance, when seeking an item in a database housing N item, quantum parallelism is harnessed to generate a superposition of all N states as shown in Fig.1. Achieving this involves a sequence of quantum gate operations.

# B. Oracle Function

Grover's algorithm hinges on the application of an oracle function, often denoted as " $U_f$ ". This oracle acts to mark the target state(s) by inverting their sign. For instance, if the objective is to locate a specific item in a database, the oracle

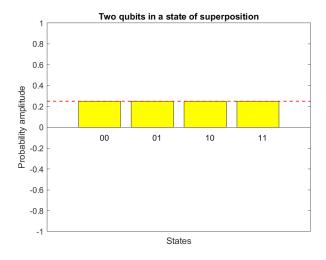


Fig. 1. Superposition of 2 qubits

would negate the amplitude corresponding to the target item. In Fig. 2, it is graphically shown the oracle function flipping the correct target.

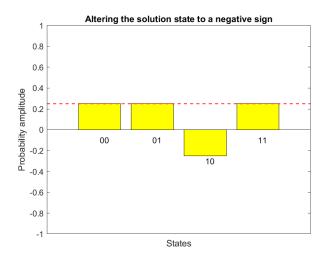


Fig. 2. Altering the sign of solution state(10)

# C. Amplitude Amplification

The core of the Grover algorithm is the process of amplitude amplification, which entails two central maneuvers:

- Inversion around the Mean: During this stage, the amplitudes are mirrored around their average value, thus boosting the amplitude of the desired state(s) while reducing the amplitudes of the non-desired states.
- **Grover diffusion operator**: In this step, the amplitudes of the target state(s) are further augmented through the application of a suite of quantum gates [10].

After acting of Grover diffusion operator, the final output will have amplified magnitude as shown in Fig. 3.

#### D. Reiteration

Step. 2 and step. 3 are iterated approximately  $\sqrt{N}$  times to maximize the likelihood of detecting the correct state. This number of iterations ensures that the probability of identifying the correct state approaches near certainty.

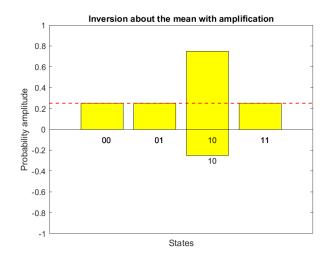


Fig. 3. Inversion about the mean with amplification.

#### E. Measurement

Ultimately, the quantum state is subjected to measurement. The target state is discerned with notably higher probability in comparison to the non-target state.

# III. CONCLUSION

This study thoroughly investigated and modeled the Mott insulator  $V_2O_3$ , exploring its potential for ReRAM technology. The impact of various electrode configurations on device performance was carefully examined, identifying crucial areas for improvement crucial for successful integration. These results are pivotal for advancing the use of Mott materials in emerging memory technologies. The insights gained from this research are particularly valuable for developing a practical, physical model for future applications.

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